HWD2161

1.1W Audio Power Amplifier with Shutdown Mode

General Description

The HWD2161 is a bridge-connected audio power amplifier capable of delivering 1.1W of continuous average power to an 8Ω load with 1% THD+N using a 5V power supply.

audio power amplifiers were designed specifically to provide high quality output power with a minimal amount of external components using surface mount packaging. Since the HWD2161 does not require output coupling capacitors, bootstrap capacitors, or snubber networks, it is optimally suited for low-power portable systems.

consumption shutdown mode, as well as an internal thermal shutdown protection mechanism.

The unity-gain stable HWD2161 can be configured by external ■ Compatible with PC power supplies gain-setting resistors for differential gains of up to 10 without the use of external compensation components. Higher gains may be achieved with suitable compensation.

Key Specifications

■ THD+N for 1kHz at 1W continuous average output power into 8Ω

1.0% (max)

■ Output power at 10% THD+N at 1kHz into 8Ω

1.5W (typ)

■ Shutdown Current

0.6µA (typ)

Features

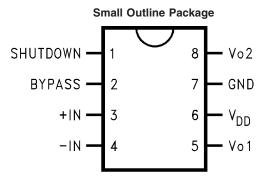
- The HWD2161 features an externally controlled, low-power No output coupling capacitors, bootstrap capacitors, or snubber circuits are necessary
 - Small Outline (SO) packaging

 - Thermal shutdown protection circuitry
 - Unity-gain stable
 - External gain configuration capability

Applications

- Personal computers
- Portable consumer products
- Self-powered speakers
- Toys and games

Connection Diagram



Top View Order Number HWD2161M

Typical Application

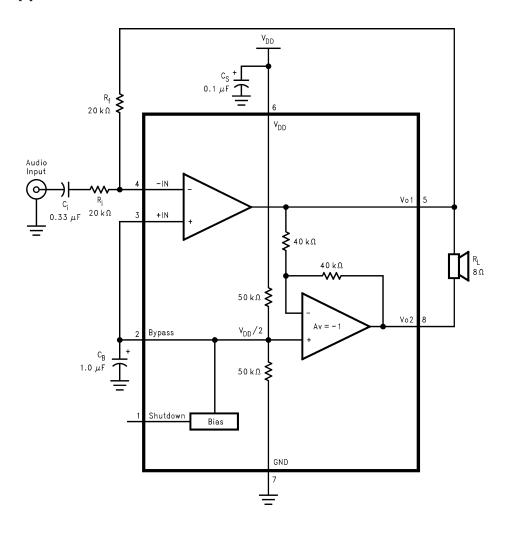


FIGURE 1. Typical Audio Amplifier Application Circuit

Absolute Maximum Ratings (Note 2)

If Military/Aerospace specified devices are required, please contact the CSMSC Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage Storage Temperature -65°C to +150°C Input Voltage -0.3V to V_{DD} + Power Dissipation (Note 3) Internally limited ESD Susceptibility (Note 4) 3000V ESD Susceptibility (Note 5) 250V Junction Temperature 150°C Soldering Information Small Outline Package Vapor Phase (60 sec.) 215°C See AN-450 "Surface Mounting and their Effects on Product Reliability" for other methods of soldering surface mount devices.

Operating Ratings

Temperature Range

 $T_{MIN} \le T_A \le T_{MAX}$ $-40^{\circ}C \le T_A \le +85^{\circ}C$

Supply Voltage $2.0V \le V_{DD} \le 5.5V$

Thermal Resistance

 $\begin{array}{lll} \theta_{JC} \ (typ) - M08A & 35^{\circ} \text{C/W} \\ \theta_{JA} \ (typ) - M08A & 140^{\circ} \text{C/W} \\ \theta_{JC} \ (typ) - N08E & 37^{\circ} \text{C/W} \end{array}$

 θ_{JA} (typ)—N08E 107°C/W

Electrical Characteristics (Note 1) (Note 2)

Infrared (15 sec.)

The following specifications apply for $V_{DD} = 5V$, unless otherwise specified. Limits apply for $T_A = 25^{\circ}C$.

220°C

			HWD2161		11
Symbol	Parameter	Conditions	Typical	Limit	Units (Limits)
			(Note 6)	(Note 7)	(Lillits)
V _{DD}	Supply Voltage			2.0	V (min)
				5.5	V (max)
I _{DD}	Quiescent Power Supply Current	$V_{IN} = 0V$, $I_O = 0A$ (Note 8)	6.5	10.0	mA (max)
I _{SD}	Shutdown Current	$V_{pin1} = V_{DD}$	0.6	10.0	μA (max)
Vos	Output Offset Voltage	$V_{IN} = 0V$	5.0	50.0	mV (max)
Po	Output Power	THD = 1% (max); f = 1 kHz	1.1	1.0	W (min)
THD+N	Total Harmonic Distortion + Noise	$P_O = 1Wrms$; 20 Hz $\leq f \leq$ 20 kHz	0.72		%
PSRR	Power Supply Rejection Ratio	V _{DD} = 4.9V to 5.1V	65		dB

Note 1: All voltages are measured with respect to the ground pin, unless otherwise specified.

Note 2: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. Electrical Characteristics state DC and AC electrical specifications under particular test conditions which guarantee specific performance limits. This assumes that the device is within the Operating Ratings. Specifications are not guaranteed for parameters where no limit is given, however, the typical value is a good indication of device performance.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature T_A . The maximum allowable power dissipation is $P_{DMAX} = (T_{JMAX} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower. For the HWD2161, $T_{JMAX} = 150^{\circ}C$, and the typical junction-to-ambient thermal resistance, when board mounted, is $140^{\circ}C/W$.

Note 4: Human body model, 100pF discharged through a 1.5k $\!\Omega$ resistor.

Note 5: Machine Model, 220pF-240pF discharged through all pins.

Note 6: Typicals are measured at 25°C and represent the parametric norm.

High Gain Application Circuit

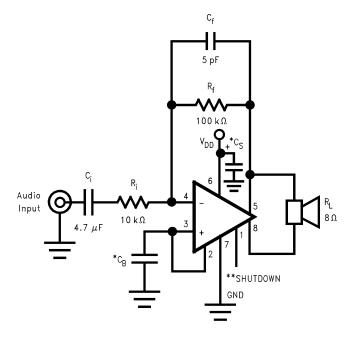
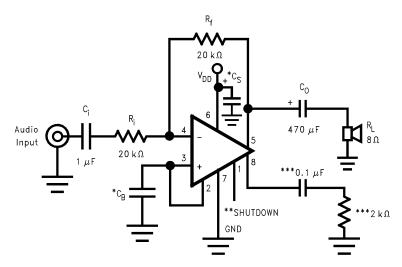


FIGURE 2. Audio Ampiifier with A_{VD} = 20

Single Ended Application Circuit



 $^{^{\}star}C_S$ and C_B size depend on specific application requirements and constraints. Typical values of C_S and C_B are 0.1 μF .

FIGURE 3. Single-Ended Amplifier with $A_{V} = -1$

^{**}Pin 1 should be connected to V_{DD} to disable the amplifier or to GND to enable the amplifier. This pin should not be left floating.

^{***}These components create a "dummy" load for pin 8 for stability purposes.

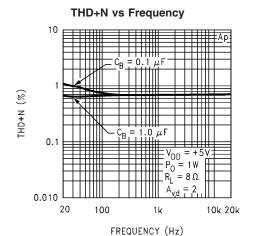
External Components Description

(Figures 1, 2)

Components	Functional Description				
1. R _i	Inverting input resistance which sets the closed-loop gain in conjunction with R _f . This resistor also forms				
	a high pass filter with C_i at $f_C = 1 / (2\pi R_i C_i)$.				
2. C _i	Input coupling capacitor which blocks DC voltage at the amplifier's input terminals. Also creates a				
	highpass filter with R_i at $f_C = 1 / (2\pi R_i C_i)$.				
3. R _f	Feedback resistance which sets closed-loop gain in conjunction with R _i .				
4. C _S	Supply bypass capacitor which provides power supply filtering. Refer to the Application Information				
	section for proper placement and selection of supply bypass capacitor.				
5. C _B	Bypass pin capacitor which provides half supply filtering. Refer to the Application Information section				
	for proper placement and selection of bypass capacitor.				
6. C _f (Note 9)	9) C _f in conjunction with R _f creates a low-pass filter which bandwidth limits the amplifier and prevents				
	possible high frequency oscillation bursts. $f_C = 1 / (2\pi R_f C_f)$				

Note 9: Optional component dependent upon specific design requirements. Refer to the Application Information section for more information.

Typical Performance Characteristics



THD+N vs Frequency

10

C_B = 0.1 μF

0.1

C_B = 1.0 μF

V_{DD} = +5V

R_L = 8.Ω

A_{Vd} = 10

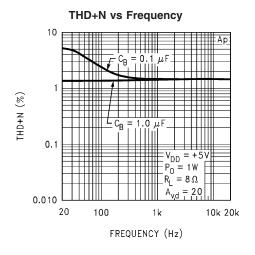
20

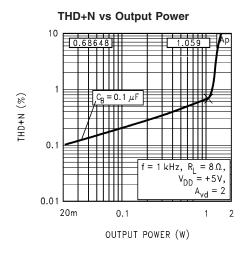
100

1k

10k 20k

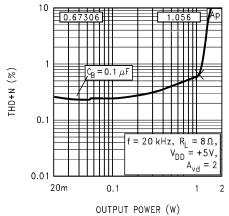
FREQUENCY (Hz)



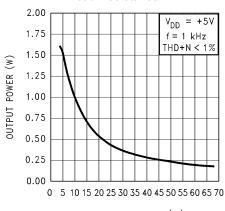


Typical Performance Characteristics (Continued)



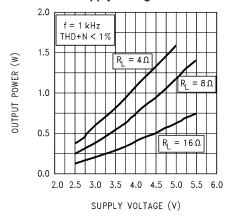


Output Power vs Load Resistance

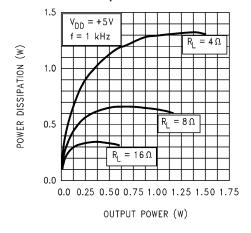


LOAD RESISTANCE (Ω)

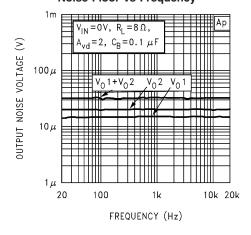
Output Power vs Supply Voltage



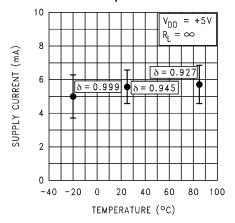
Power Dissipation vs Output Power



Noise Floor vs Frequency

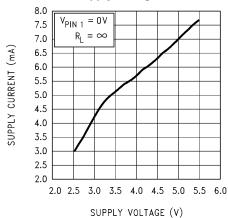


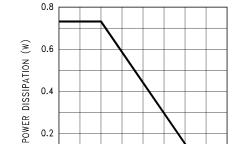
Supply Current Distribution vs Temperature



Typical Performance Characteristics (Continued)





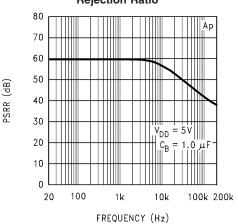


Power Derating Curve

AMBIENT TEMPERATURE (°C)

175

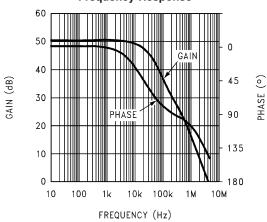
Power Supply Rejection Ratio



Open Loop Frequency Response

0.0

-25



Application Information

BRIDGE CONFIGURATION EXPLANATION

As shown in Figure 1 , the HWD2161 has two operational amplifiers internally, allowing for a few different amplifier configurations. The first amplifier's gain is externally configurable, while the second amplifier is internally fixed in a unity-gain, inverting configuration. The closed-loop gain of the first amplifier is set by selecting the ratio of $R_{\rm f}$ to $R_{\rm i}$ while the second amplifier's gain is fixed by the two internal $40 k\Omega$ resistors. Figure 1 shows that the output of amplifier one serves as the input to amplifier two which results in both amplifiers producing signals identical in magnitude, but out of phase 180° . Consequently, the differential gain for the IC is:

$$A_{vd} = 2 * (R_f / R_i)$$

By driving the load differentially through outputs $V_{\rm O1}$ and $V_{\rm O2}$, an amplifier configuration commonly referred to as "bridged mode" is established. Bridged mode operation is different from the classical single-ended amplifier configuration where one side of its load is connected to ground.

A bridge amplifier design has a few distinct advantages over the single-ended configuration, as it provides differential drive to the load, thus doubling output swing for a specified supply voltage. Consequently, four times the output power is possible as compared to a single-ended amplifier under the same conditions. This increase in attainable output power assumes that the amplifier is not current limited or clipped. In order to choose an amplifier's closed-loop gain without causing excessive clipping which will damage high frequency transducers used in loudspeaker systems, please refer to the **Audio Power Amplifier Design** section.

A bridge configuration, such as the one used in Audio Power Amplifiers, also creates a second advantage over single-ended amplifiers. Since the differential outputs, V_{O1} and V_{O2}, are biased at half-supply, no net DC voltage exists across the load. This eliminates the need for an output coupling capacitor which is required in a single supply, single-ended amplifier configuration. Without an output coupling capacitor in a single supply, single-ended amplifier, the half-supply bias across the load would result in both increased internal IC power dissipation and also permanent loudspeaker damage. An output coupling capacitor forms a high pass filter with the load requiring that a large value such as $470\mu F$ be used with an 8Ω load to preserve low frequency response. This combination does not produce a flat response down to 20Hz, but does offer a compromise between printed circuit board size and system cost, versus low frequency response.

POWER DISSIPATION

Power dissipation is a major concern when designing a successful amplifier, whether the amplifier is bridged or single-ended. A direct consequence of the increased power delivered to the load by a bridge amplifier is an increase in internal power dissipation. Equation 1 states the maximum power dissipation point for a bridge amplifier operating at a given supply voltage and driving a specified output load.

$$P_{DMAX} = 4*(V_{DD})^2 / (2\pi^2 R_L)$$
 (1)

Since the HWD2161 has two operational amplifiers in one package, the maximum internal power dissipation is 4 times that of a single-ended amplifier. Even with this substantial increase in power dissipation, the HWD2161 does not require heatsinking. From Equation 1, assuming a 5V power supply and an 8Ω load, the maximum power dissipation point is

625mW.The maximum power dissipation point obtained from Equation 1 must not be greater than the power dissipation that results from Equation 2:

$$P_{DMAX} = (T_{JMAX} - T_A) / \theta_{JA}$$
 (2)

For the HWD2161 surface mount package, $\Re = 140^{\circ}$ C/W and $T_{JMAX} = 150$ °C. Depending on the ambient temperature, T_A , of the system surroundings, Equation 2 can be used to find the maximum internal power dissipation supported by the IC packaging. If the result of Equation 1 is greater than that of Equation 2, then either the supply voltage must be decreased or the load impedance increased. For the typical application of a 5V power supply, with an 8Ω load, the maximum ambient temperature possible without violating the maximum junction temperature is approximately 62.5°C provided that device operation is around the maximum power dissipation point. Power dissipation is a function of output power and thus, if typical operation is not around the maximum power dissipation point, the ambient temperature can be increased. Refer to the Typical Performance Characteristics curves for power dissipation information for lower output powers.

POWER SUPPLY BYPASSING

As with any power amplifier, proper supply bypassing is critical for low noise performance and high power supply rejection. The capacitor location on both the bypass and power supply pins should be as close to the device as possible. As displayed in the **Typical Performance Characteristics** section, the effect of a larger half supply bypass capacitor is improved low frequency THD+N due to increased half-supply stability. Typical applications employ a 5V regulator with $10\mu F$ and a $0.1\mu F$ bypass capacitors which aid in supply stability, but do not eliminate the need for bypassing the supply nodes of the HWD2161. The selection of bypass capacitors, especially C_B , is thus dependant upon desired low frequency THD+N, system cost, and size constraints

SHUTDOWN FUNCTION

In order to reduce power consumption while not in use, the HWD2161 contains a shutdown pin to externally turn off the amplifier's bias circuitry. The shutdown feature turns the amplifier off when a logic high is placed on the shutdown pin. Upon going into shutdown, the output is immediately disconnected from the speaker. A typical guiescent current of 0.6µA results when the supply voltage is applied to the shutdown pin. In many applications, a microcontroller or microprocessor output is used to control the shutdown circuitry which provides a quick, smooth transition into shutdown. Another solution is to use a single-pole, single-throw switch that when closed, is connected to ground and enables the amplifier. If the switch is open, then a soft pull-up resistor of 47kΩ will disable the HWD2161. There are no soft pull-down resistors inside the HWD2161, so a definite shutdown pin voltage must be applied externally, or the internal logic gate will be left floating which could disable the amplifier unexpectedly.

HIGHER GAIN AUDIO AMPLIFIER

The HWD2161 is unity-gain stable and requires no external components besides gain-setting resistors, an input coupling capacitor, and proper supply bypassing in the typical application. However, if a closed-loop differential gain of greater than 10 is required, a feedback capacitor may be needed, as shown in *Figure 2*, to bandwidth limit the amplifier. This feedback capacitor creates a low pass filter that eliminates

Application Information (Continued)

possible high frequency oscillations. Care should be taken when calculating the -3dB frequency in that an incorrect combination of R_f and C_f will cause rolloff before 20kHz. A typical combination of feedback resistor and capacitor that will not produce audio band high frequency rolloff is $R_f=100\text{k}\Omega$ and $C_f=5\text{pF}.$ These components result in a -3dB point of approximately 320kHz. Once the differential gain of the amplifier has been calculated, a choice of R_f will result, and C_f can then be calculated from the formula stated in the <code>External Components Description</code> section.

VOICE-BAND AUDIO AMPLIFIER

Many applications, such as telephony, only require a voice-band frequency response. Such an application usually requires a flat frequency response from 300Hz to 3.5kHz. By adjusting the component values of $\it Figure~2$, this common application requirement can be implemented. The combination of R_i and C_i form a highpass filter while R_f and C_f form a lowpass filter. Using the typical voice-band frequency range, with a passband differential gain of approximately 100, the following values of $R_i,~C_i,~R_f,~and~C_f$ follow from the equations stated in the $\it External~Components~Description$ section.

$$R_i = 10k\Omega$$
, $R_f = 510k$, $C_i = 0.22\mu F$, and $C_f = 15pF$

Five times away from a -3dB point is 0.17dB down from the flatband response. With this selection of components, the resulting -3dB points, f_L and f_H , are 72Hz and 20kHz, respectively, resulting in a flatband frequency response of better than $\pm 0.25dB$ with a rolloff of 6dB/octave outside of the passband. If a steeper rolloff is required, other common bandpass filtering techniques can be used to achieve higher order filters.

SINGLE-ENDED AUDIO AMPLIFIER

Although the typical application for the HWD2161 is a bridged monoaural amp, it can also be used to drive a load singleendedly in applications, such as PC cards, which require that one side of the load is tied to ground. Figure 3 shows a common single-ended application, where V_{O1} is used to drive the speaker. This output is coupled through a 470µF capacitor, which blocks the half-supply DC bias that exists in all single-supply amplifier configurations. This capacitor, designated $C_{\rm O}$ in Figure 3, in conjunction with $R_{\rm L}$, forms a highpass filter. The -3dB point of this high pass filter is $1/(2\pi R_1 C_0)$, so care should be taken to make sure that the product of R₁ and C_O is large enough to pass low frequencies to the load. When driving an 8Ω load, and if a full audio spectrum reproduction is required, $C_{\rm O}$ should be at least $470\mu\text{F. V}_{\text{O2}}$, the output that is not used, is connected through a 0.1 μ F capacitor to a $2k\Omega$ load to prevent instability. While such an instability will not affect the waveform of V_{O1}, it is good design practice to load the second output.

AUDIO POWER AMPLIFIER DESIGN

Design a 1W / 8Ω Audio Amplifier

Given:

Power Output 1 Wrms Load Impedance 8Ω Input Level 1 Vrms Input Impedance 20 k Ω Bandwidth 100 Hz–20 kHz \pm 0.25 dB

A designer must first determine the needed supply rail to obtain the specified output power. By extrapolating from the Output Power vs Supply Voltage graph in the **Typical Performance Characteristics** section, the supply rail can be easily found. A second way to determine the minimum supply rail is to calculate the required $V_{\rm opeak}$ using Equation 3 and add the dropout voltage. Using this method, the minimum supply voltage would be $(V_{\rm opeak} + V_{\rm OD}$, where $V_{\rm OD}$ is typically 0.6V.

$$v_{\text{opeak}} = \sqrt{(2R_{L}P_{0})}$$
(3)

For 1W of output power into an 8Ω load, the required V_{opeak} is 4.0V. A minumum supply rail of 4.6V results from adding V_{opeak} and V_{od} . But 4.6V is not a standard voltage that exists in many applications and for this reason, a supply rail of 5V is designated. Extra supply voltage creates dynamic headroom that allows the HWD2161 to reproduce peaks in excess of 1Wwithout clipping the signal. At this time, the designer must make sure that the power supply choice along with the output impedance does not violate the conditions explained in the **Power Dissipation** section.

Once the power dissipation equations have been addressed, the required differential gain can be determined from Equation 4.

$$A_{VD} \ge \sqrt{(P_0 R_L)} / (V_{IN}) = V_{orms} / V_{inrms}$$
(4)

$$R_f/R_i = A_{VD} / 2 \tag{5}$$

From equation 4, the minimum A_{vd} is 2.83: $A_{vd} = 3$

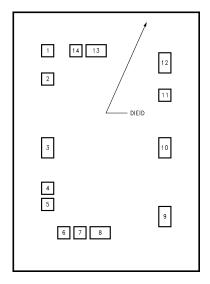
Since the desired input impedance was $20k\Omega$, and with a A_{vd} of 3, a ratio of 1:1.5 of R_f to R_i results in an allocation of R_i = $20k\Omega$, R_f = $30k\Omega$. The final design step is to address the bandwidth requirements which must be stated as a pair of -3dB frequency points. Five times away from a -3db point is 0.17dB down from passband response which is better than the required $\pm 0.25dB$ specified. This fact results in a low and high frequency pole of 20Hz and 100kHz respectively. As stated in the **External Components** section, R_i in conjunction with C_i create a highpass filter.

$$C_i \ge 1 / (2\pi^* 20k\Omega^* 20Hz) = 0.397\mu F$$
; use $0.39\mu F$.

The high frequency pole is determined by the product of the desired high frequency pole, $f_{\rm H},$ and the differential gain, $A_{\rm vd}.$ With a $A_{\rm vd}=2$ and $f_{\rm H}=100{\rm kHz},$ the resulting GBWP = 100kHz which is much smaller than the HWD2161 GBWP of 4MHz. This figure displays that if a designer has a need to design an amplifier with a higher differential gain, the HWD2161 can still be used without running into bandwidth problems.

HWD2161 MDA MWA

1.1W Audio Power Amplifier with Shutdown Mode



Die Layout (B - Step)

DIE/WAFER CHARACTERISTICS

Fabrication Attributes	General Die Information		
Physical Die Identification	HWD2161B	Bond Pad Opening Size (min)	83µm x 83µm
Die Step	В	Bond Pad Metalization	ALUMINUM
Physical Attributes	Passivation	VOM NITRIDE	
Wafer Diameter	150mm	Back Side Metal	BARE BACK
Dise Size (Drawn)	1372µm x 2032µm	Back Side Connection	GND
	54.0mils x 80.0mils		
Thickness	406µm Nominal		
Min Pitch	108µm Nominal		

Special Assembly Requirements:

Note: Actual die size is rounded to the nearest micron.

		Die Bond Pad Co	ordinate Location	s (B - Step)			
	(Referenced to die	e center, coordinat	es in μm) NC = N	o Connection, N.U.	= Not Used		
SIGNAL NAME	PAD# NUMBER	X/Y COORDINATES		PAD SIZE			
		Х	Υ	Х		Υ	
SHUTDOWN	1	-425	710	83	х	83	
BYPASS	2	-445	499	83	х	83	
NC	3	-445	-34	83	х	170	
NC	4	-445	-383	83	х	83	
INPUT +	5	-445	-492	83	х	83	
INPUT -	6	-352	-710	83	х	83	
GND	7	-243	-710	83	Х	83	
Vo1	8	-91	-710	170	х	83	
GND	9	445	-574	83	х	170	
VDD	10	445	-2	83	х	170	
NC	11	445	387	83	х	83	
GND	12	445	633	83	Х	170	
Vo2	13	-63	710	170	Х	83	
GND	14	-215	710	83	Х	83	

